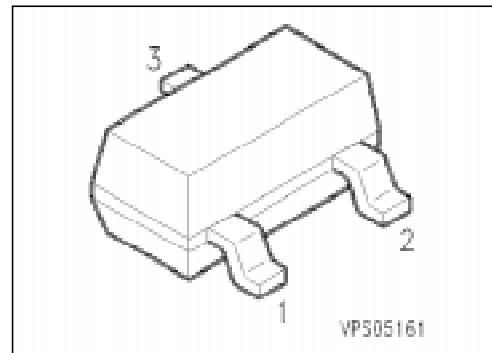


NPN Silicon AF Transistors

**BCW 60
BCX 70**

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types: BCW 61, BCX 71 (PNP)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package ¹⁾
			1	2	3	
BCW 60 A	AAs	Q62702-C1517	B	E	C	SOT-23
BCW 60 B	ABs	Q62702-C1497				
BCW 60 C	ACs	Q62702-C1476				
BCW 60 D	ADs	Q62702-C1477				
BCW 60 FF	AFs	Q62702-C1529				
BCW 60 FN	ANs	Q62702-C1567				
BCX 70 G	AGs	Q62702-C1539				
BCX 70 H	AHs	Q62702-C1481				
BCX 70 J	AJs	Q62702-C1552				
BCX 70 K	AKs	Q62702-C1571				

¹⁾ For detailed information see chapter Package Outlines.

Maximum Ratings

Parameter	Symbol	Values			Unit	
		BCW 60	BCW 60 FF	BCX 70		
Collector-emitter voltage	V_{CEO}	32	32	45	V	
Collector-base voltage	V_{CB0}	32	32	45		
Emitter-base voltage	V_{EB0}	5				
Collector current	I_C	100			mA	
Peak collector current	I_{CM}	200				
Peak base current	I_{BM}	200				
Total power dissipation, $T_S = 71 \text{ }^\circ\text{C}$	P_{tot}	330			mW	
Junction temperature	T_j	150			$^\circ\text{C}$	
Storage temperature range	T_{stg}	– 65 ... + 150				

Thermal Resistance

Junction - ambient ¹⁾	$R_{th JA}$	≤ 310	K/W
Junction - soldering point	$R_{th JS}$	≤ 240	

¹⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 10 \text{ mA}$	$V_{(\text{BR})\text{CE}0}$	32 45	— —	— —	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$	$V_{(\text{BR})\text{CB}0}$	32 45	— —	— —	
Emitter-base breakdown voltage $I_E = 1 \mu\text{A}$	$V_{(\text{BR})\text{EB}0}$	5	—	—	
Collector cutoff current $V_{CB} = 32 \text{ V}$	I_{CB0}	—	—	20	nA
$V_{CB} = 45 \text{ V}$		—	—	20	nA
$V_{CB} = 32 \text{ V}, T_A = 150^\circ\text{C}$	BCW 60, BCW 60 FF	—	—	20	μA
$V_{CB} = 45 \text{ V}, T_A = 150^\circ\text{C}$	BCX 70	—	—	20	μA
Emitter cutoff current $V_{EB} = 4 \text{ V}$	I_{EB0}	—	—	20	nA
DC current gain ¹⁾ $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$	h_{FE}	20 20 40 100	140 200 300 460	— — — —	—
BCW 60 A, BCX 70 G		120	170	220	
BCW 60 B, BCX 70 H		180	250	310	
BCW 60 FF, BCW 60 C, BCX 70 J		250	350	460	
BCW 60 FN, BCW 60 D, BCX 70 K		380	500	630	
$I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$		50 70 90 100	— — — —	— — — —	
BCW 60 A, BCX 70 G		—	—	—	
BCW 60 B, BCX 70 H		—	—	—	
BCW 60 FF, BCW 60 C, BCX 70 J		—	—	—	
BCW 60 FN, BCW 60 D, BCX 70 K		—	—	—	
$I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}$		—	—	—	
BCW 60 A, BCX 70 G		—	—	—	
BCW 60 B, BCX 70 H		—	—	—	
BCW 60 FF, BCW 60 C, BCX 70 J		—	—	—	
BCW 60 FN, BCW 60 D, BCX 70 K		—	—	—	

¹⁾ Pulse test: $t \leq 300 \mu\text{s}$, $D \leq 2 \%$.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	V_{CEsat}	— —	0.12 0.20	0.25 0.55	V
Base-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	V_{BEsat}	— —	0.70 0.83	0.85 1.05	
Base-emitter voltage $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}$ ¹⁾	$V_{BE(\text{on})}$	— 0.55 —	0.52 0.65 0.78	— 0.75 —	

AC characteristics

Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	—	250	—	MHz
Output capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{obo}	—	3	—	pF
Input capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	C_{ibo}	—	8	—	
Short-circuit input impedance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCW 60 A, BCX 70 G BCW 60 B, BCX 70 H BCW 60 FF, BCW 60 C, BCX 70 J BCW 60 FN, BCW 60 D, BCX 70 K	h_{11e}	— — — —	2.7 3.6 4.5 7.5	— — — —	kΩ
Open-circuit reverse voltage transfer ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCW 60 A, BCX 70 G BCW 60 B, BCX 70 H BCW 60 FF, BCW 60 C, BCX 70 J BCW 60 FN, BCW 60 D, BCX 70 K	h_{12e}	— — — —	1.5 2.0 2.0 3.0	— — — —	10^{-4}

¹⁾ Pulse test: $t \leq 300 \mu\text{s}$, $D \leq 2 \%$.

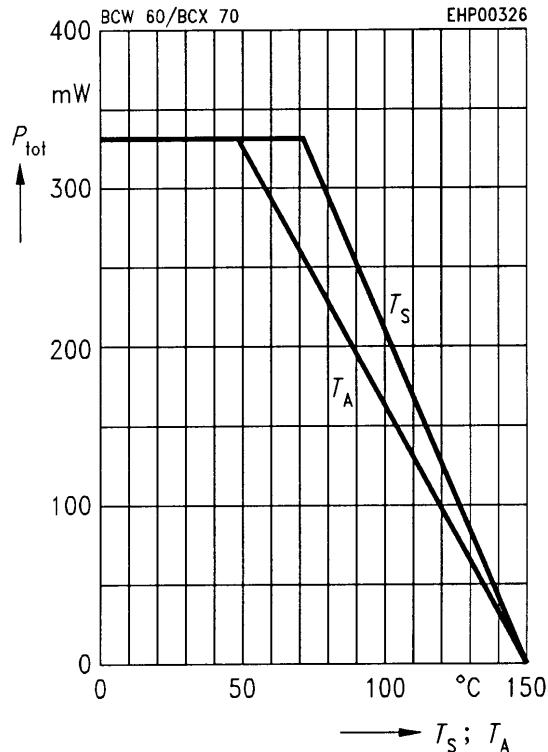
Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

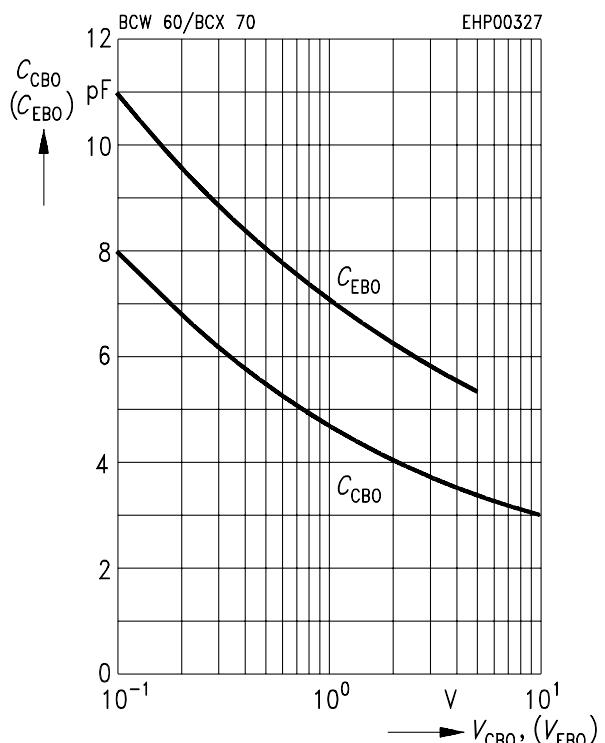
AC characteristics

Short-circuit forward current transfer ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCW 60 A, BCX 70 G BCW 60 B, BCX 70 H BCW 60 FF, BCW 60 C, BCX 70 J BCW 60 FN, BCW 60 D, BCX 70 K	h_{21e}	—	200	—	—
Open-circuit output admittance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCW 60 A, BCX 70 G BCW 60 B, BCX 70 H BCW 60 FF, BCW 60 C, BCX 70 J BCW 60 FN, BCW 60 D, BCX 70 K	h_{22e}	—	18	—	μs
Noise figure $I_C = 0.2 \text{ mA}, V_{CE} = 5 \text{ V}, R_S = 2 \text{ k}\Omega$ $f = 1 \text{ kHz}, \Delta f = 200 \text{ Hz}$ BCW 60 A to BCX 70 K BCW 60 FF, BCW 60 FN	F	—	2	—	dB
Equivalent noise voltage $I_C = 0.2 \text{ mA}, V_{CE} = 5 \text{ V}, R_S = 2 \text{ k}\Omega$ $f = 10 \text{ Hz} \dots 50 \text{ Hz}$ BCW 60 FF, BCW 60 FN	V_n	—	1	2	μV

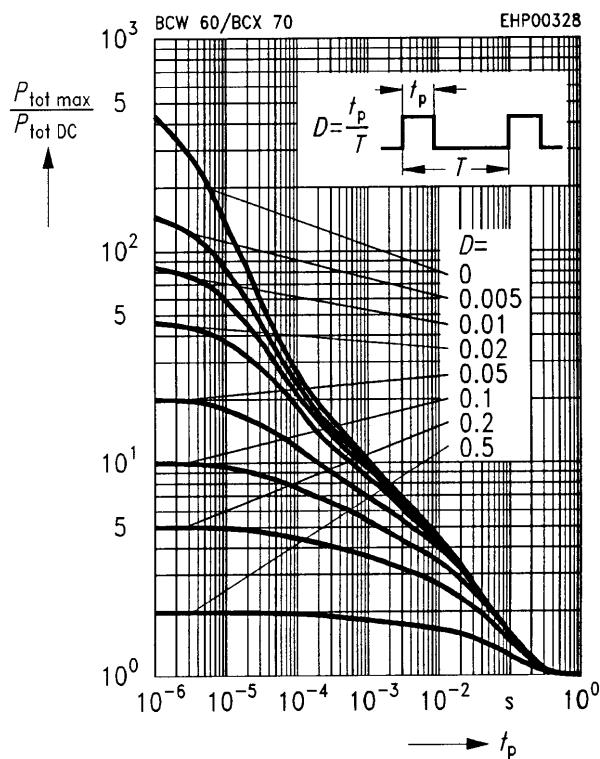
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$
 * Package mounted on epoxy



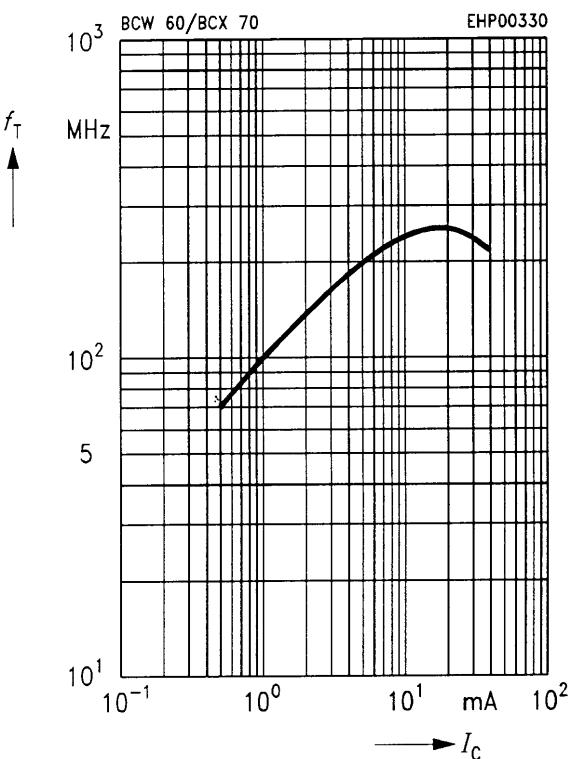
Collector-base capacitance $C_{\text{CBO}} = f(V_{\text{CBO}})$
Emitter-base capacitance $C_{\text{EBO}} = f(V_{\text{EBO}})$



Permissible pulse load $P_{\text{tot max}}/P_{\text{tot DC}} = f(t_p)$



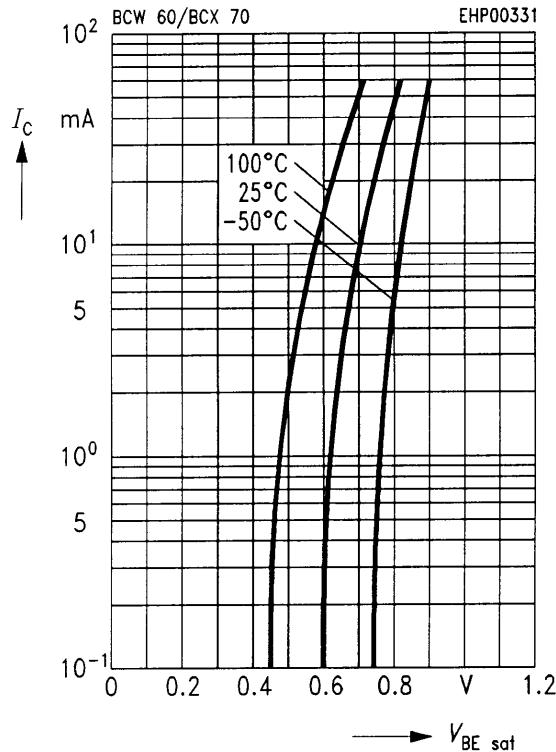
Transition frequency $f_T = f(I_C)$
 $V_{\text{CE}} = 5 \text{ V}$



Base-emitter saturation voltage

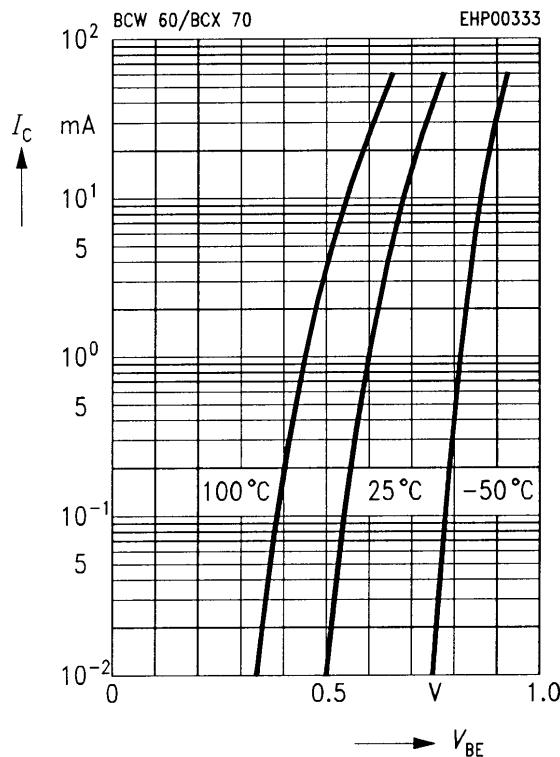
$$I_C = f(V_{BEsat})$$

$$h_{FE} = 40$$



Collector current $I_C = f(V_{BE})$

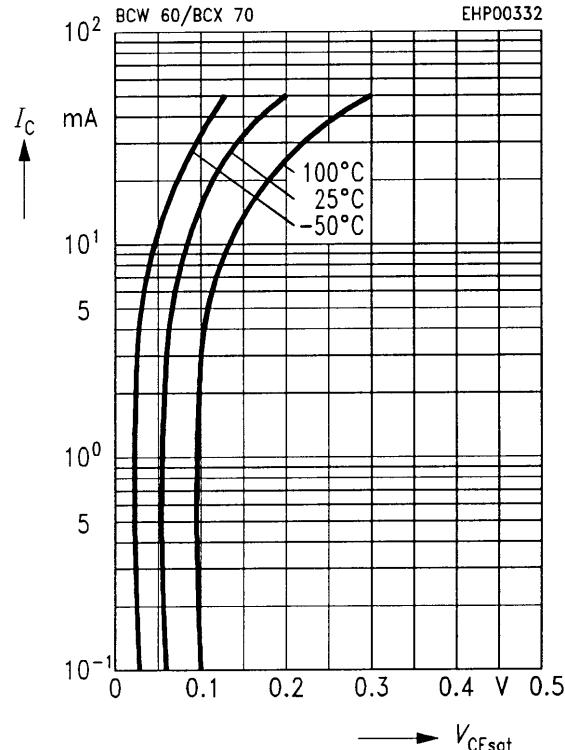
$$V_{CE} = 5 \text{ V}$$



Collector-emitter saturation voltage

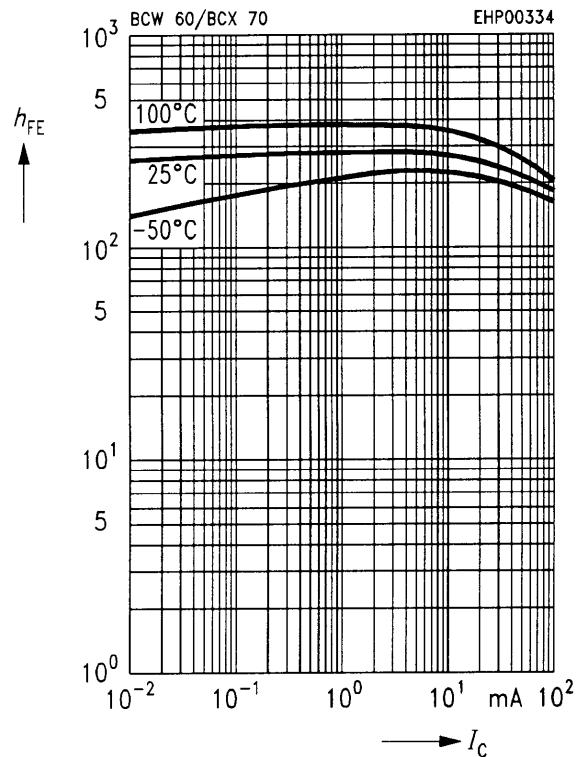
$$I_C = f(V_{CEsat})$$

$$h_{FE} = 40$$

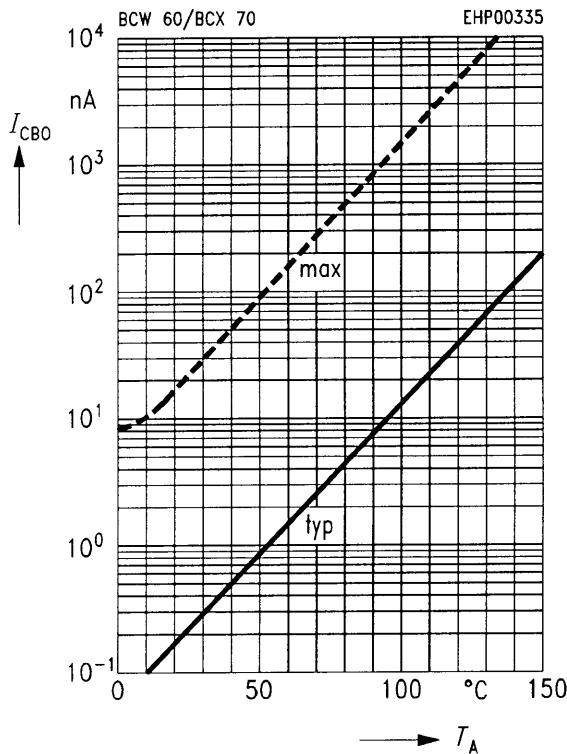


DC current gain $h_{FE} = f(I_C)$

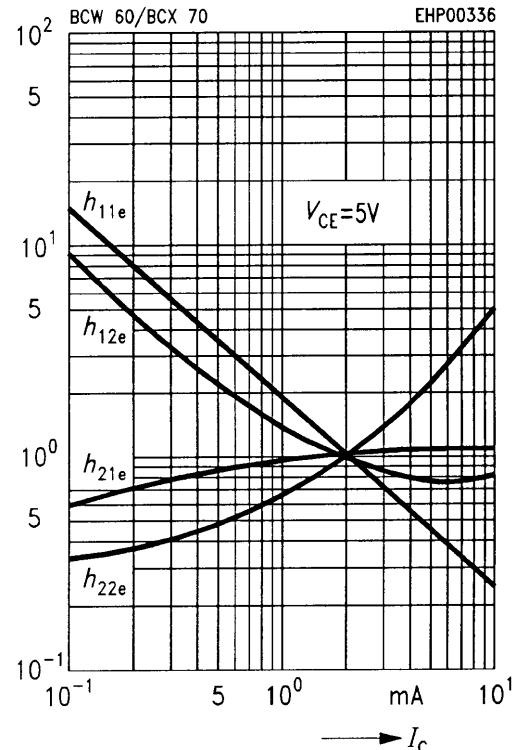
$$V_{CE} = 5 \text{ V}$$



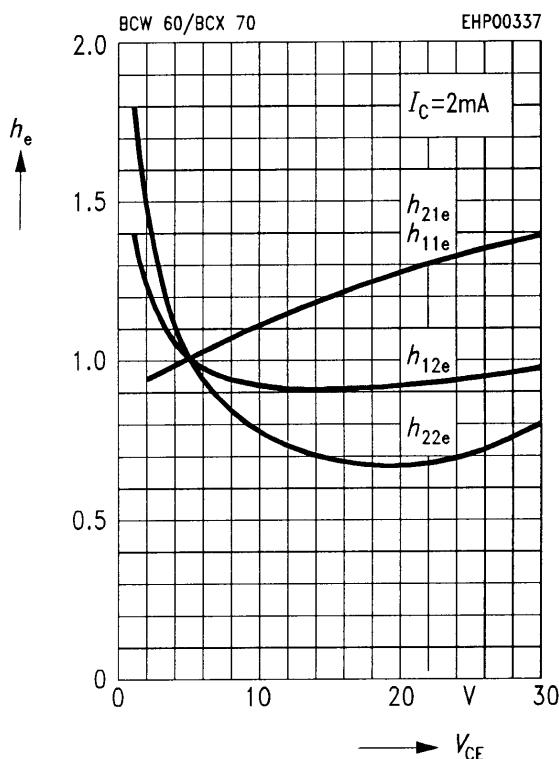
Collector cutoff current $I_{CB0} = f(T_A)$



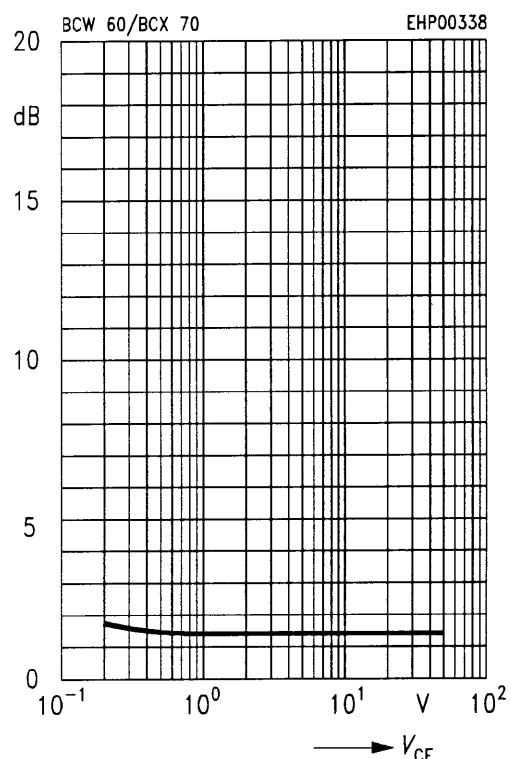
h parameter $h_e = f(I_C)$
 $V_{CE} = 5$ V



h parameter $h_e = f(V_{CE})$
 $I_C = 2$ mA

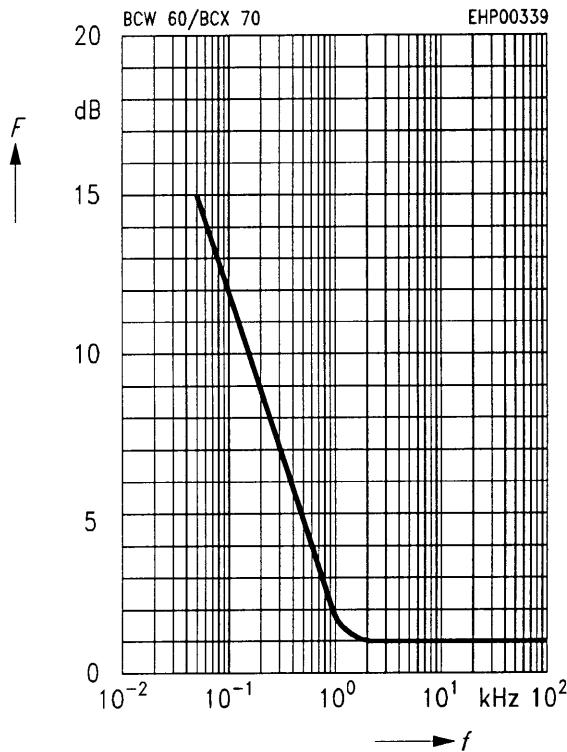


Noise figure $F = f(V_{CE})$
 $I_C = 0.2$ mA, $R_S = 2$ kΩ, $f = 1$ kHz



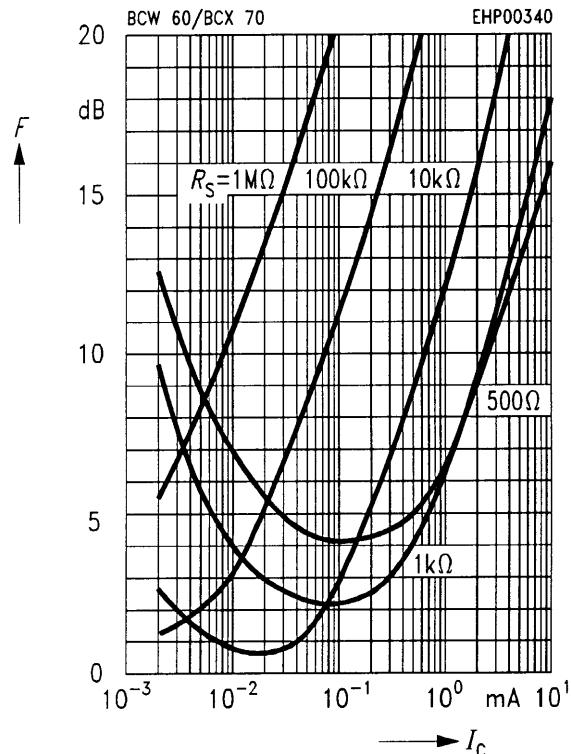
Noise figure $F = f(f)$

$I_C = 0.2 \text{ mA}$, $R_S = 2 \text{ k}\Omega$, $V_{CE} = 5 \text{ V}$



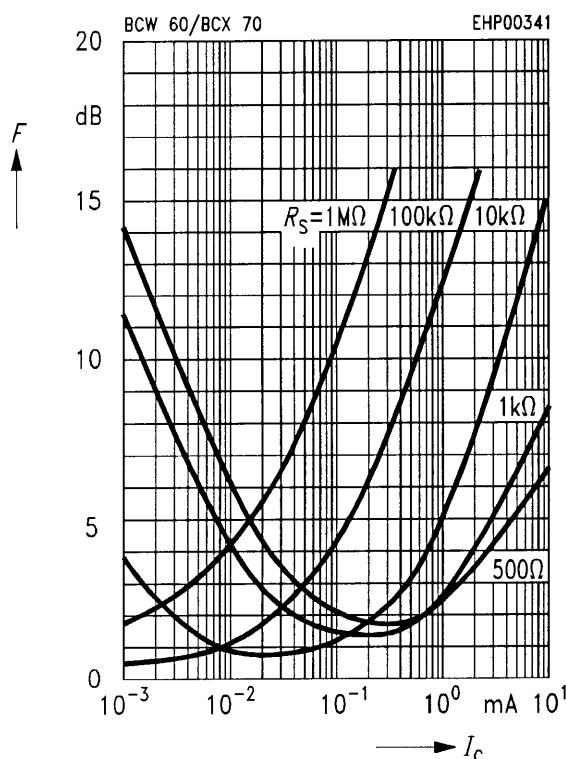
Noise figure $F = f(I_C)$

$V_{CE} = 5 \text{ V}$, $f = 120 \text{ Hz}$



Noise figure $F = f(I_C)$

$V_{CE} = 5 \text{ V}$, $f = 1 \text{ kHz}$



Noise figure $F = f(I_C)$

$V_{CE} = 5 \text{ V}$, $f = 10 \text{ kHz}$

